

Serial No.: New Application

IN THE CLAIMS:

1. (Original) A contact formation method comprising:
forming a film comprising Si and Ti on a surface of a
layer of a Group III nitride semiconductor; and
heat-treating the film and the semiconductor layer.
2. (Original) The contact formation method as set forth
in claim 1, wherein the film formation is performed by
depositing Si and Ti in this order.
3. (Presently Amended) The contact formation method as
set forth in claim 1 or 2, wherein a heat treatment
temperature is in the range of 500°C to 1100°C.
4. (Original) A semiconductor device comprising:
a Group III nitride semiconductor layer into which Si is
diffused as an impurity by a heat treatment performed after a
film comprising Si and Ti is formed on a surface of the Group
III nitride semiconductor layer; and

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an electrode film of $TiSi_2$ formed by a reaction between Ti
and Si.